

FIG. 1

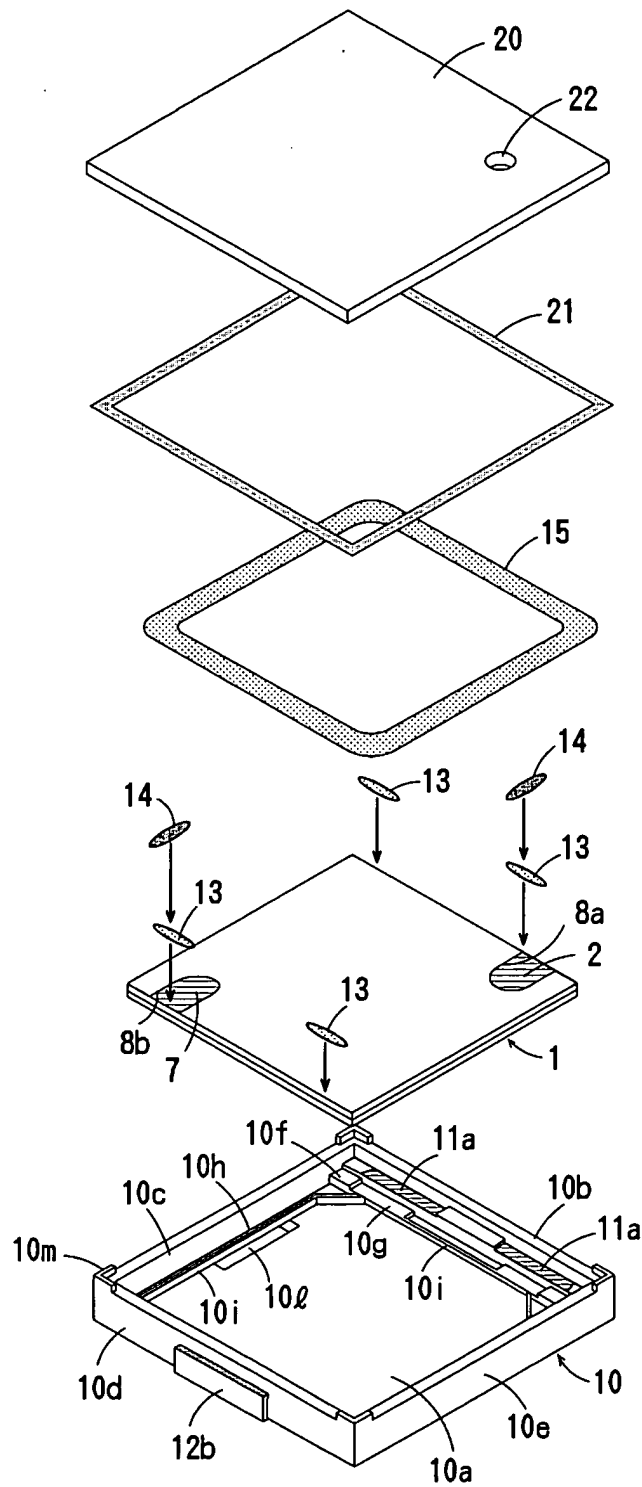


FIG. 2

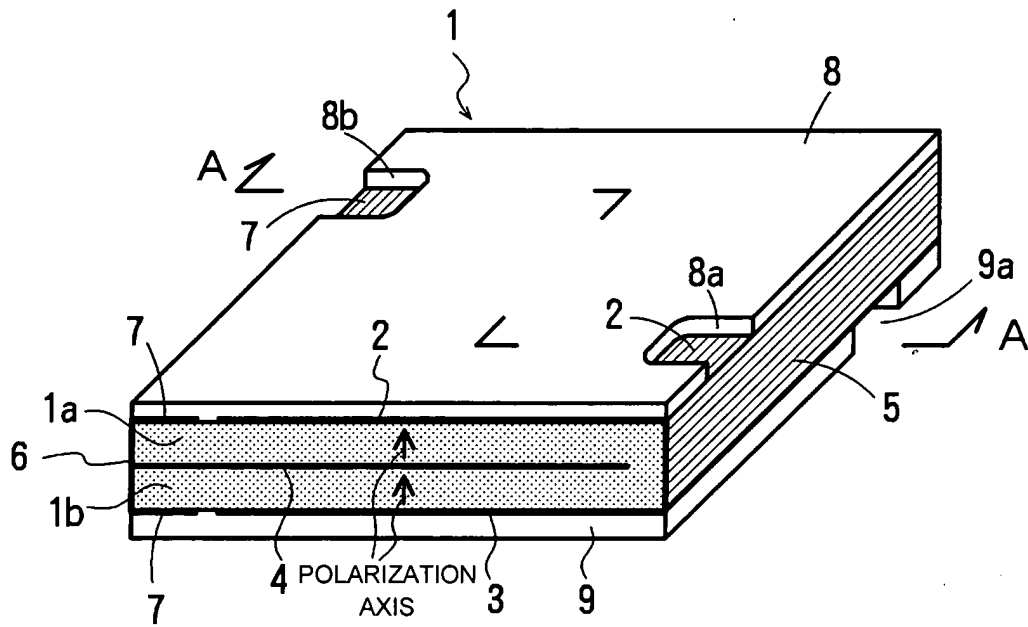


FIG. 3

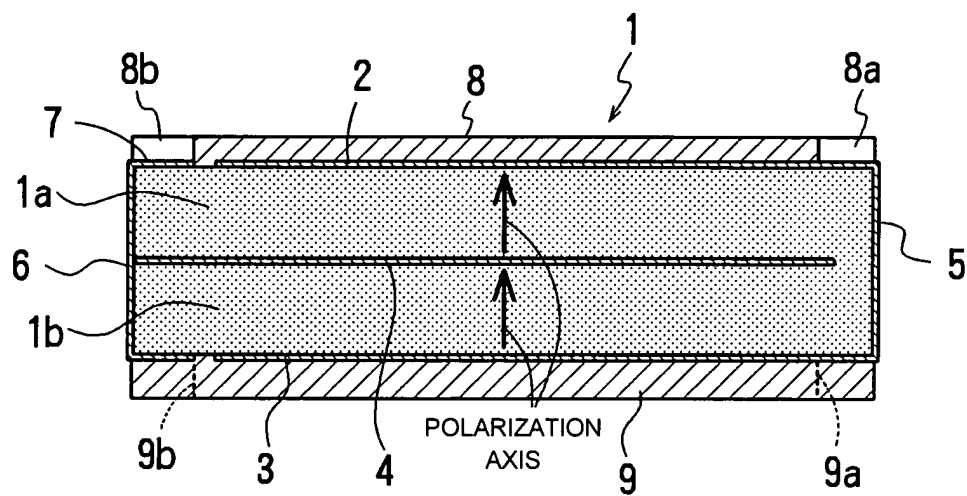
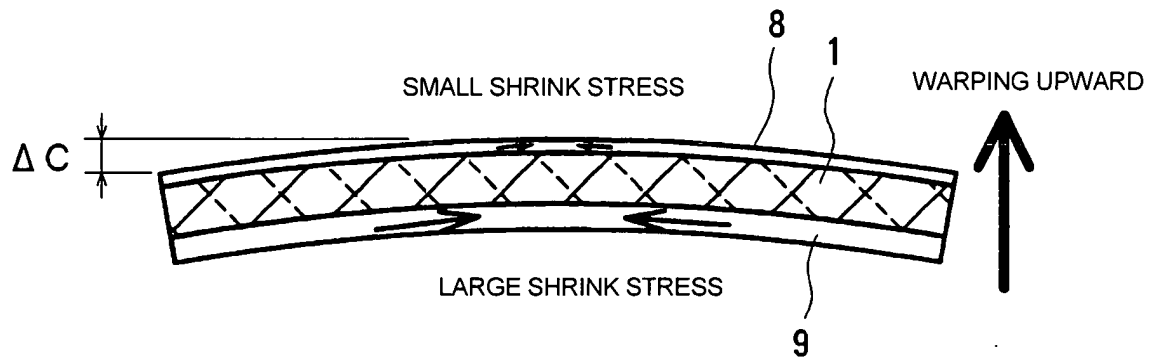


FIG. 4



[illegible]

A perspective view of a semiconductor device 10. The device features a substrate 10a with a top surface 10e and side surfaces 10h. A central rectangular region contains a patterned layer 10g. Surrounding this are several raised structures: a large L-shaped block 10j at the front-left, a smaller rectangular block 10i at the back-left, and another rectangular block 10i at the front-right. On the right side, there is a complex assembly including a textured rectangular block 11a, a small rectangular block 11, and a series of thin layers or wires 10f. At the very top edge, two small rectangular protrusions are labeled 10n and 10m. Various other labels like 10k point to specific edges or interfaces.

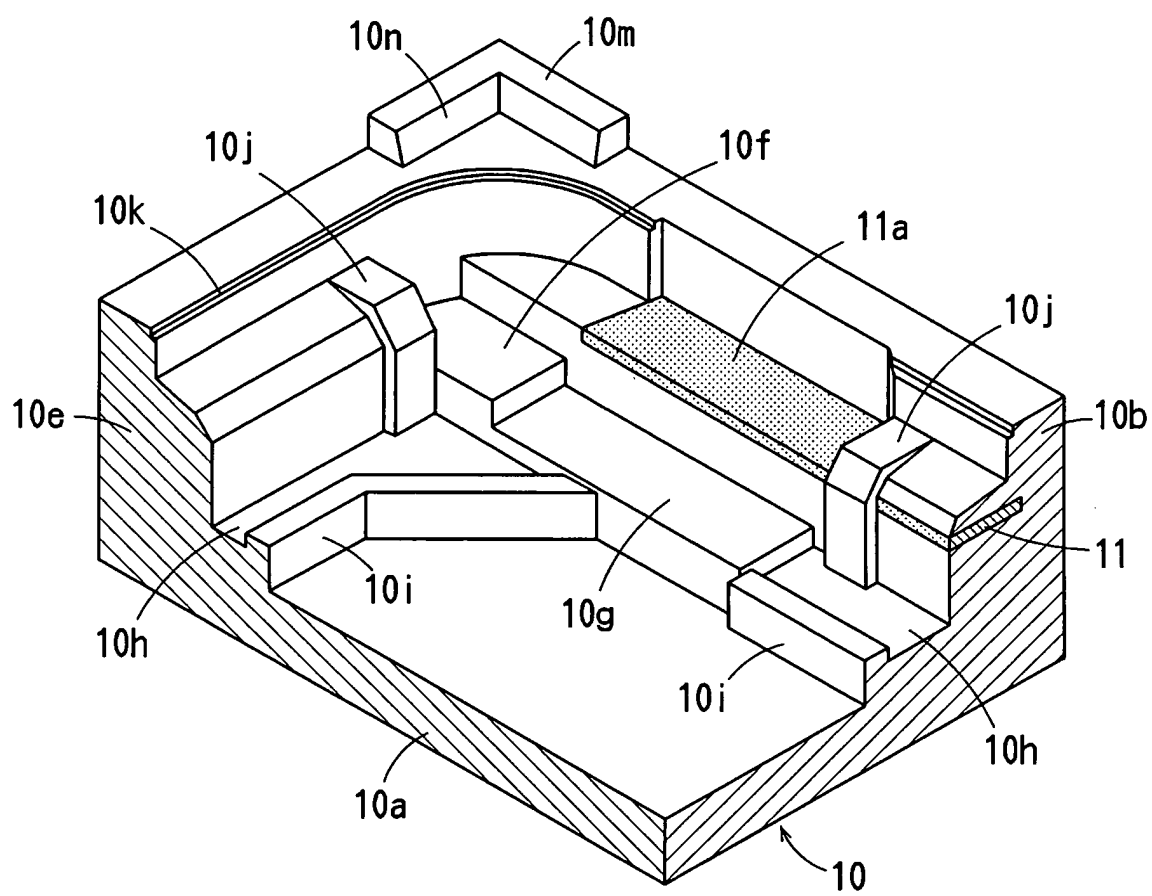


FIG. 7

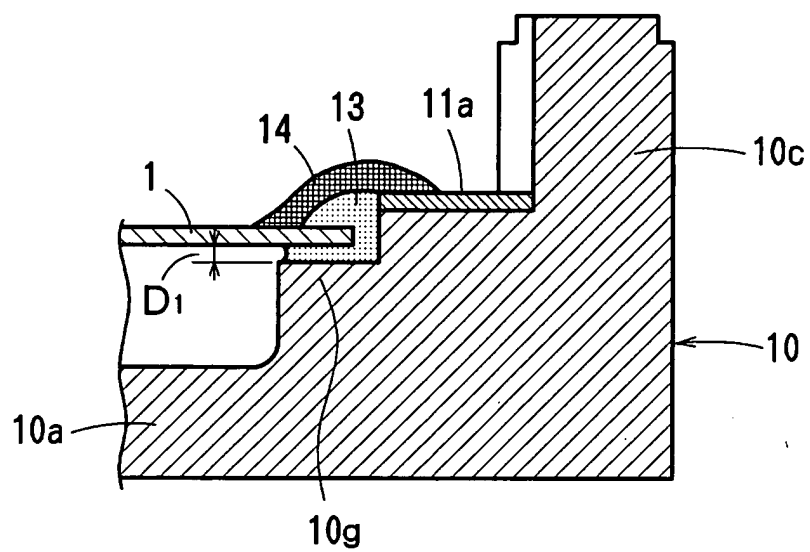


FIG. 8

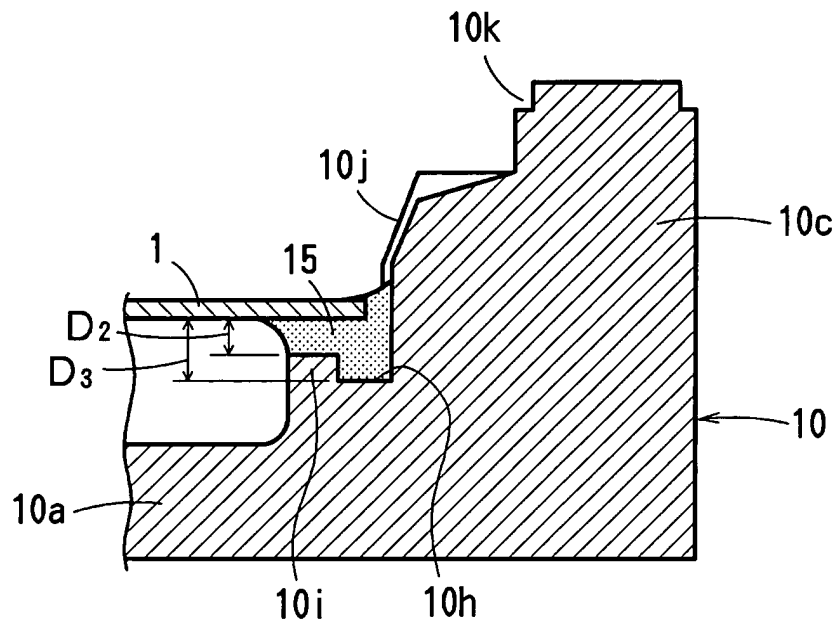


FIG. 9

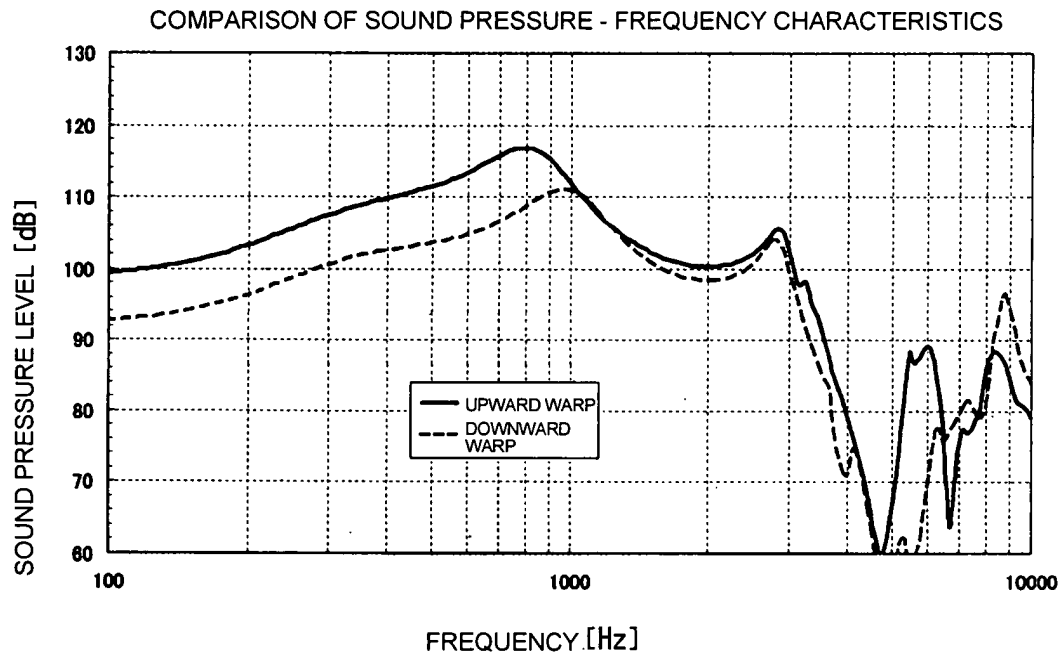


FIG. 10
PRIOR ART

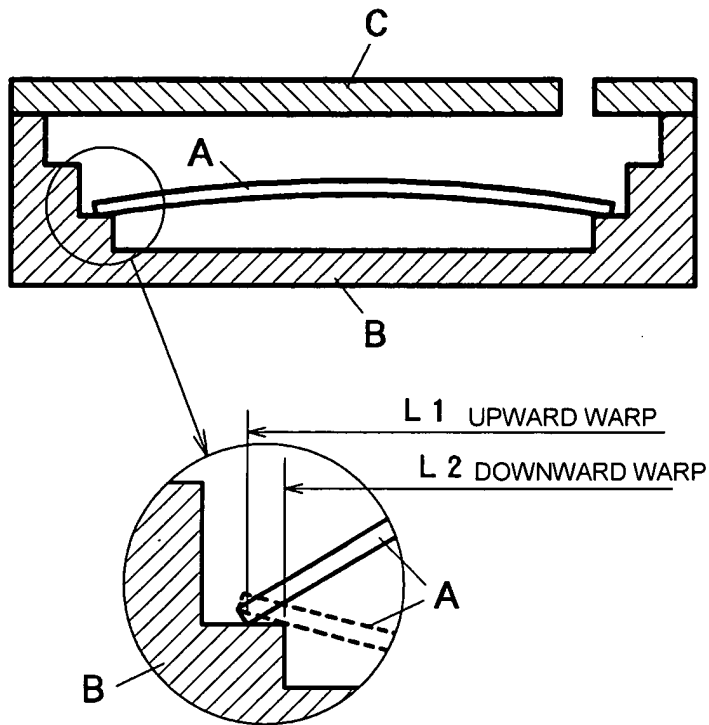


FIG. 11
PRIOR ART

